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A B S T R A C T

A METHOD OF OBTAINING A SELF-SUPPORTED THIN SEMICONDUCTOR LAYER FOR ELECTRONIC CIRCUITS

The invention relates to a method of producing a self-supported thin layer of a semiconductor material supporting at least one electronic component and/or circuit (3) on one of its faces, from a wafer (1) of said material, said wafer having a front face (2) supporting or for supporting at least one electronic component and/or circuit (3) and a rear face (4'). The method is remarkable in that it comprises steps consisting in: a) implanting atomic species in the interior of said wafer (1), from its rear face (4, 4') to obtain a zone of weakness (5) defining a front portion (6) extending from said front face (2) of said zone of weakness (5) and a rear portion (7) formed by the remainder of the wafer (1); b) detaching said rear portion (7) from the front portion (6); and c) if necessary, repeating steps a) and b) on the rear face of said front portion (6) until said front portion has the desired thickness for constituting said self-supported thin layer.

Translation of the title and the abstract as they were when originally filed by the Applicant. No account has been taken of any changes that may have been made subsequently by the PCT Authorities acting ex officio, e.g. under PCT Rules 37.2, 38.2, and/or 48.3.

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